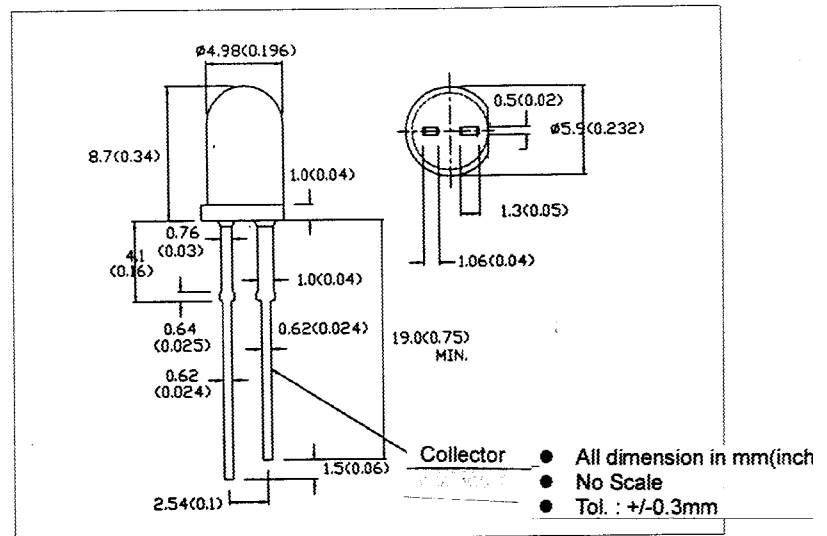


MEL79 is NPN silicon planar photo-transistor with 5mm clear transparent lens. It features ultra high illumination sensitivity and fast response time.



ABSOLUTE MAXIMUM RATINGS

Collector-Emitter Voltage	VCEO	30V
Emitter-Collector Voltage	VECO	5V
Continuous Power Dissipation	Pd	50mW
Operating Junction Temperature	Tj	-40 to +85°C
Storage Temperature Range	Tstg	-40 to +100°C
Lead Soldering Temperature (5 second, 1/16 inch from body)		260°C

ELECTRO-OPTICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	CONDITIONS
Collector-Emitter Breakdown Voltage	BVCEO	30		V	IC=100μA Ee=0
Emitter-Collector Breakdown Voltage	BVECO	5		V	IC=100μA Ee=0
Dark Current	ID		200	nA	VCE=10V Ee=0
Light Current	IL *	6.0		mA	VCE=5V Ee=5mW/cm ²
Collector-Emitter Saturation Voltage	VCE(sat)		0.3	V	IC=500μA Ee=20mW/cm ²
Rise Time	Tr	15	TYP	μs	VCE=5V IC=1mA RL=1Kohm
Fall Time	Tf	15	TYP	μs	VCE=5V IC=1mA RL=1Kohm

* : Measured at noted irradiance as emitted from a tungsten filament lamp at a color temperature of 2354°K.



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